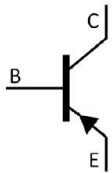


TO-92LM PNP Silicon PNP transistor in a TO-92LM Plastic Package.

Low $V_{CE(sat)}$.

Low frequency amplifier, electronic governor applications.

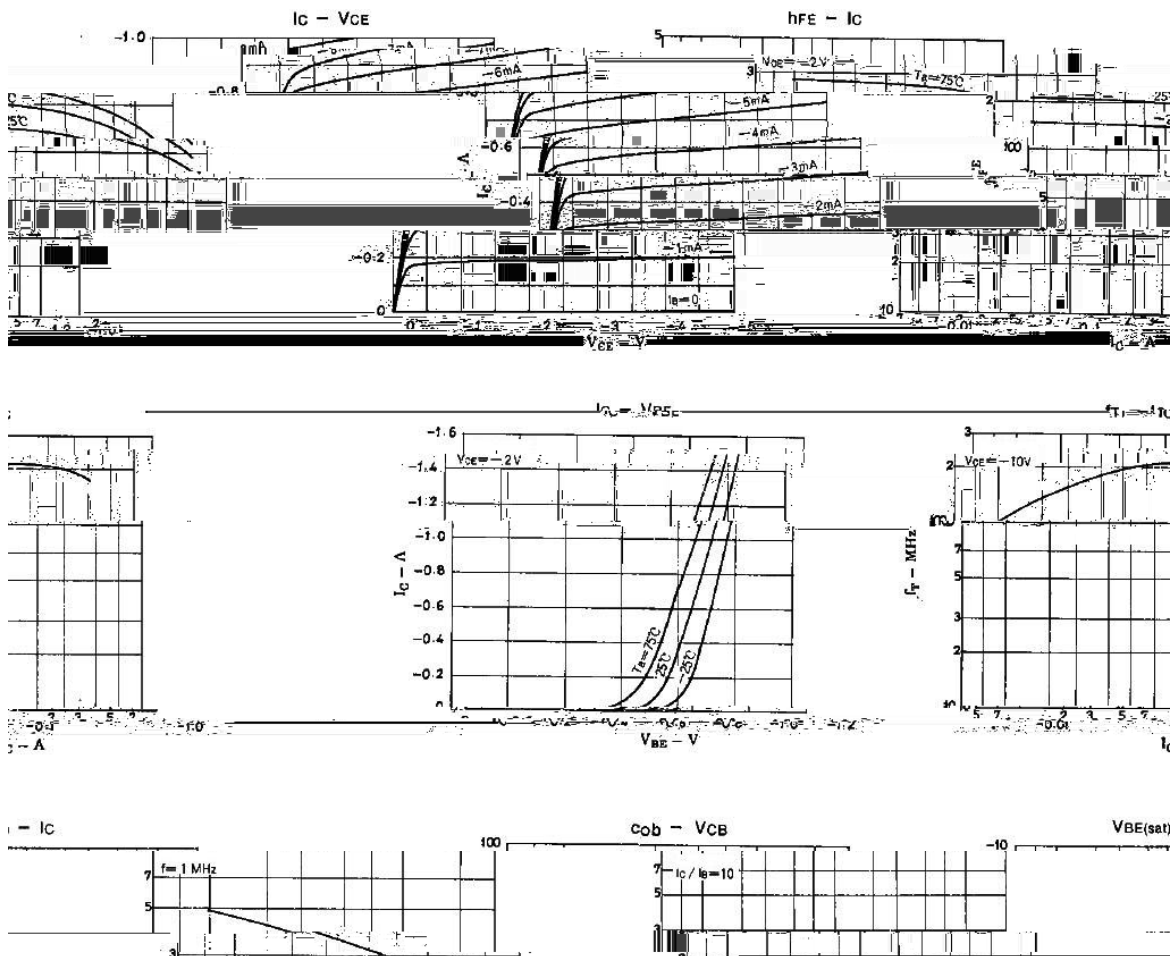


PIN1 Base PIN 2 Collector PIN 3 Emitter

h_{FE} Classifications Symbol	R	S	T
h_{FE} Range	100~200	140~280	200~400

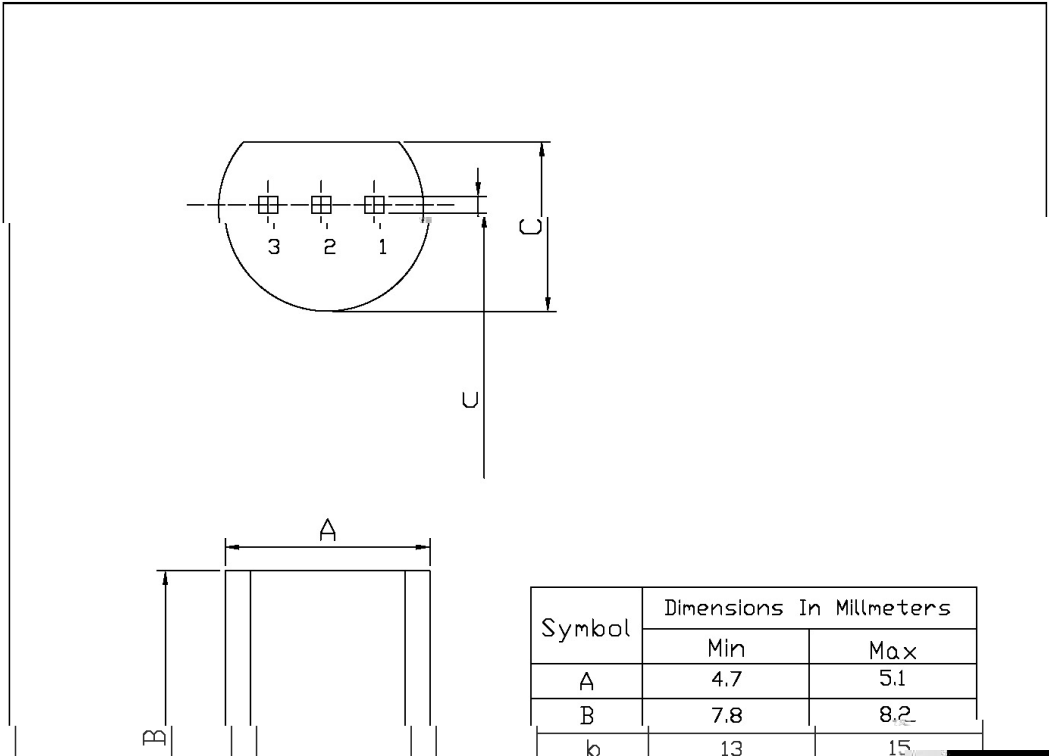
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-1.5	A
Collector Current – Continuous(Pulse)	I_{CP}	-3.0	A
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

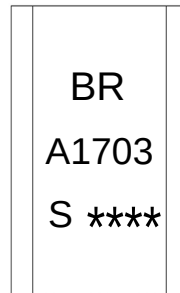
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -10\mu A$ $I_E = 0$	-30			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -10\mu A$ I_C				



TO-92LM

Unit: mm





BR:

A1703

S: h_{FE}

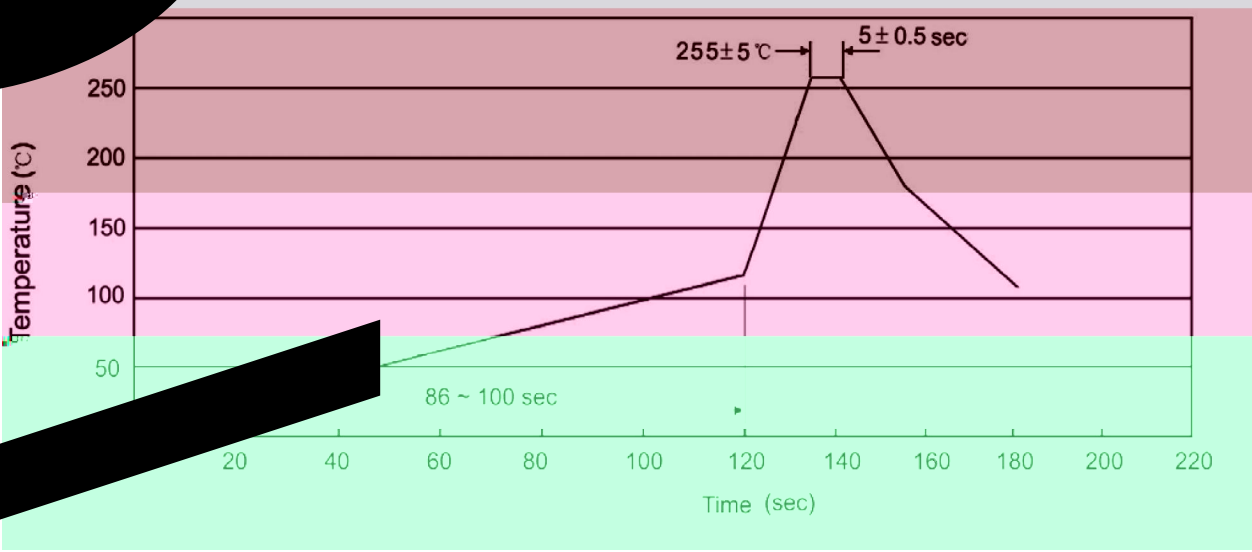
Note:

BR: Company Code.

A1703: Product Type.

S: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.



Note:

1. Preheating: 25~150 °C, Time: 60~90sec;
2. Peak Temp.: 255±5 °C, Duration: 5±0.5sec;
3. Cooling Speed: 2~10 °C/sec.

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255±5 °C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10 °C/sec.

Temp.: 270±5 °C Time: 10±1 sec

/ BULK

Package Type	Units	Dimension (unit: mm ³)		
		Bag	Inner Box	Outer Box
R13A10G1m287a1202	500	130x100x100	287x120x102	500x245x185